



PD55025-E PD55025S-E

RF POWER transistor, LdmoST plastic family
N-channel enhancement-mode, lateral MOSFETs

Features

- Excellent thermal stability
- Common source configuration
- $P_{OUT} = 25\text{ W}$ with 14.5dB gain @ 500 MHz / 12.5 V
- New RF plastic package

Description

The device is a common source N-channel, enhancement-mode lateral field-effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 12 V in common source mode at frequencies up to 1 GHz. The device boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the first true SMD plastic RF power package, PowerSO-10RF. The device's superior linearity performance makes it an ideal solution for car mobile radio. The PowerSO-10 plastic package, designed to offer high reliability, is the first ST JEDEC approved, high power SMD package. It has been specially optimized for RF needs and offers excellent RF performance and ease of assembly. Mounting recommendations are available in www.st.com/rf/ (look for application note AN1294).

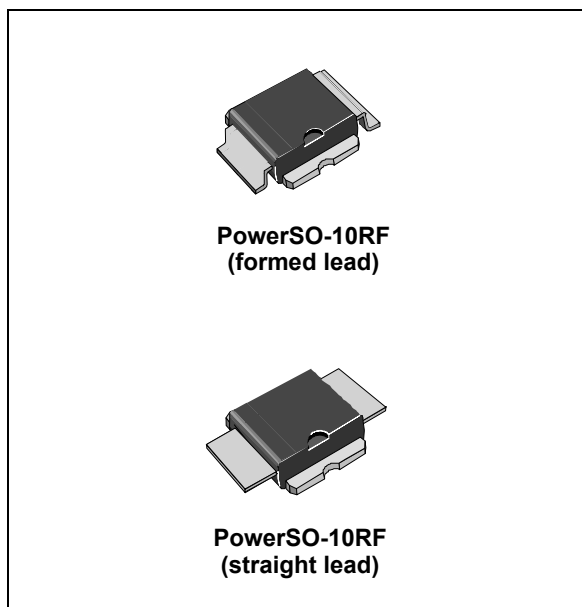


Figure 1. Pin connection

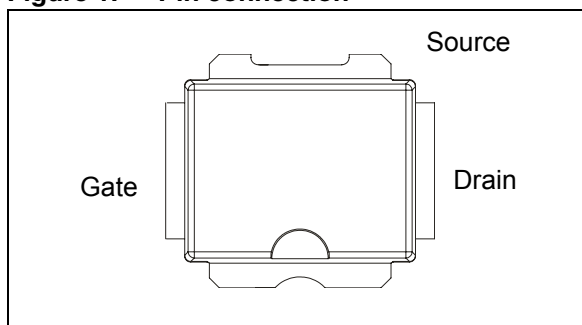


Table 1. Device summary

Order code	Package	Packing
PD55025-E	PowerSO-10RF (formed lead)	Tube
PD55025S-E	PowerSO-10RF (straight lead)	Tube
PD55015TR-E	PowerSO-10RF (formed lead)	Tape and reel
PD55015STR-E	PowerSO-10RF (straight lead)	Tape and reel

Contents

1	Electrical data	3
1.1	Maximum ratings	3
1.2	Thermal data	3
2	Electrical characteristics	4
2.1	Static	4
2.2	Dynamic	4
2.3	Moisture sensitivity level	4
3	Impedance	5
4	Typical performance	6
5	Test circuit	11
6	Circuit layout	12
7	Common source s-parameter	14
8	Package mechanical data	17
9	Revision history	22

1 Electrical data

1.1 Maximum ratings

Table 2. Absolute maximum ratings ($T_{CASE} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current	7	A
P_{DISS}	Power dissipation (@ $T_C = 70^{\circ}C$)	79	W
T_J	Max. operating junction temperature	165	$^{\circ}C$
T_{STG}	Storage temperature	-65 to +150	$^{\circ}C$

1.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Junction - case thermal resistance	1.2	$^{\circ}C/W$

2 Electrical characteristics

$T_{CASE} = +25\text{ }^{\circ}\text{C}$

2.1 Static

Table 4. Static

Symbol	Test conditions		Min.	Typ.	Max.	Unit
I_{DSS}	$V_{GS} = 0$	$V_{DS} = 28\text{ V}$			1	μA
I_{GSS}	$V_{GS} = 20\text{ V}$	$V_{DS} = 0$			1	μA
$V_{GS(Q)}$	$V_{DS} = 28\text{ V}$	$I_D = 100\text{ mA}$	2.0		5.0	V
$V_{DS(ON)}$	$V_{GS} = 10\text{ V}$	$I_D = 3\text{ A}$		0.7	0.8	V
G_{FS}	$V_{DS} = 10\text{ V}$	$I_D = 3\text{ A}$	2.5			mho
C_{ISS}	$V_{GS} = 0$	$V_{DS} = 12.5\text{ V}$		86		pF
C_{OSS}	$V_{GS} = 0$	$V_{DS} = 12.5\text{ V}$		76		pF
C_{RSS}	$V_{GS} = 0$	$V_{DS} = 12.5\text{ V}$		5.8		pF

2.2 Dynamic

Table 5. Dynamic

Symbol	Test conditions		Min.	Typ.	Max.	Unit
P_{OUT}	$V_{DD} = 12.5\text{ V}$, $I_{DQ} = 200\text{ mA}$	$f = 500\text{ MHz}$	25			W
G_P	$V_{DD} = 12.5\text{ V}$, $I_{DQ} = 200\text{ mA}$, $P_{OUT} = 25\text{ W}$, $f = 500\text{ MHz}$			14.5		dB
h_D	$V_{DD} = 12.5\text{ V}$, $I_{DQ} = 200\text{ mA}$, $P_{OUT} = 25\text{ W}$, $f = 500\text{ MHz}$			50		%
Load mismatch	$V_{DD} = 15.5\text{ V}$, $I_{DQ} = 200\text{ mA}$, $P_{OUT} = 25\text{ W}$, $f = 500\text{ MHz}$ All phase angles		20:1			VSWR

2.3 Moisture sensitivity level

Table 6. Moisture sensitivity level

Test methodology	Rating
J-STD-020B	MSL 3

3 Impedance

Figure 2. Current conventions



Table 7. Impedance data

Freq. (MHz)	$Z_{IN} (\Omega)$	$Z_{DL}(\Omega)$
175	$3.20 - j 4.41$	$1.56 + j 2.14$
480	$1.01 - j 1.67$	$1.06 + j 0.22$
500	$0.93 - j 1.53$	$1.12 + j 0.20$
520	$0.88 - j 1.98$	$1.07 + j 0.83$

4 Typical performance

Figure 3. Capacitance vs supply voltage

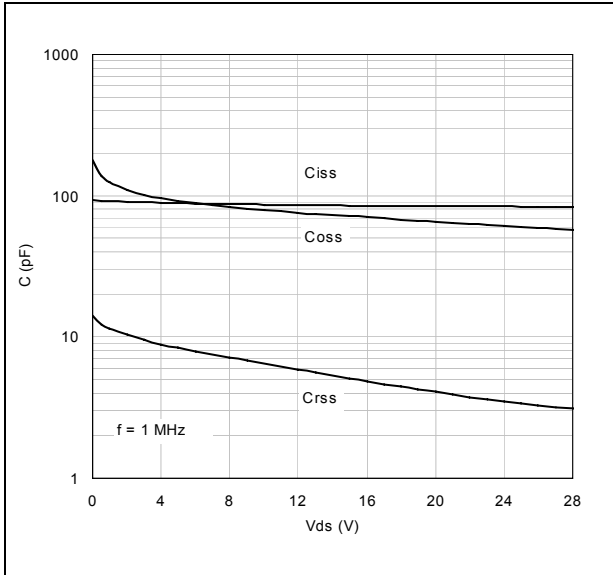


Figure 4. Drain current vs gate source voltage

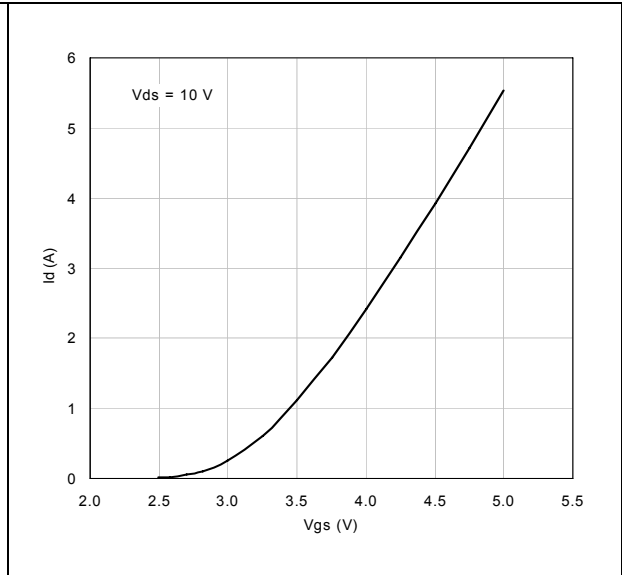


Figure 5. Gate-source voltage vs case temperature

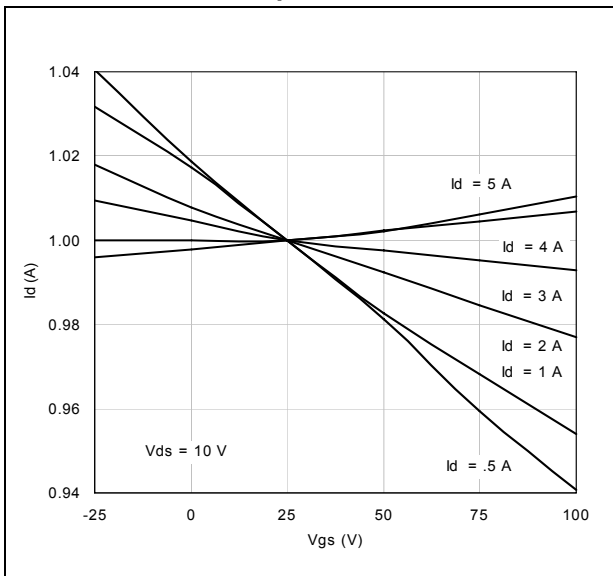


Figure 6. Output power vs input power

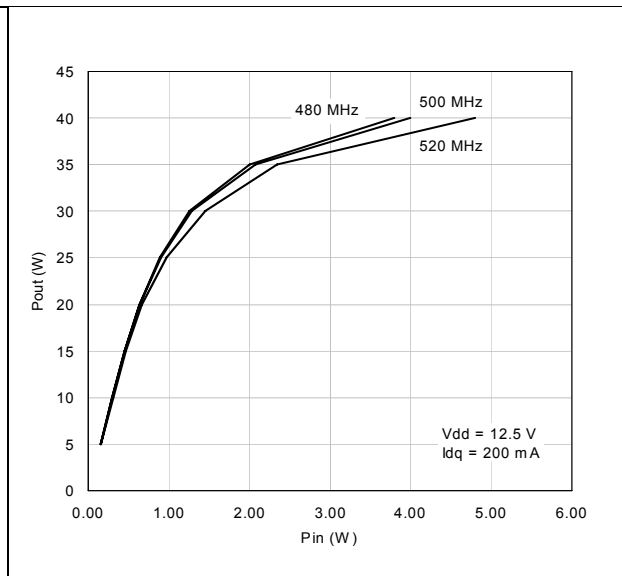


Figure 7. Output power vs input power

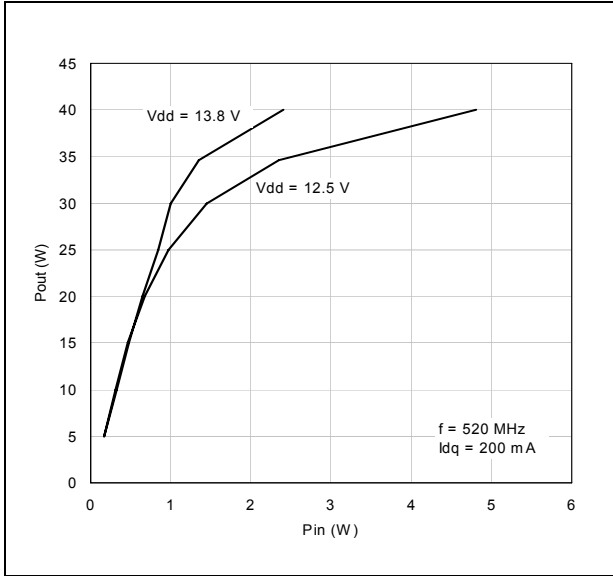


Figure 8. Power gain vs. output power

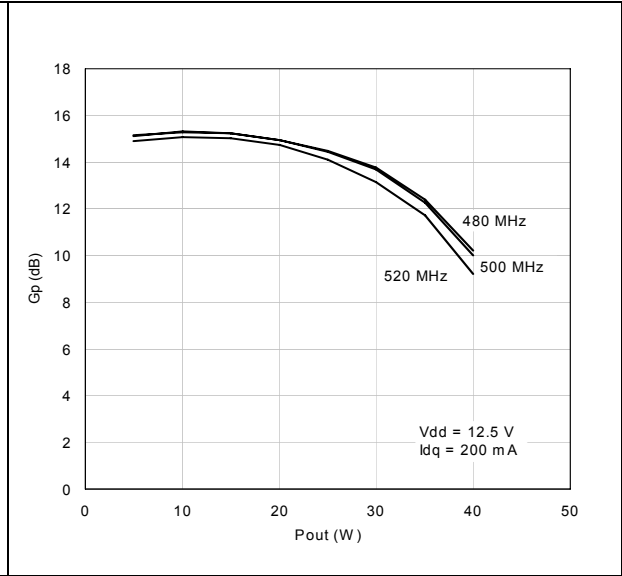


Figure 9. Drain efficiency vs output power

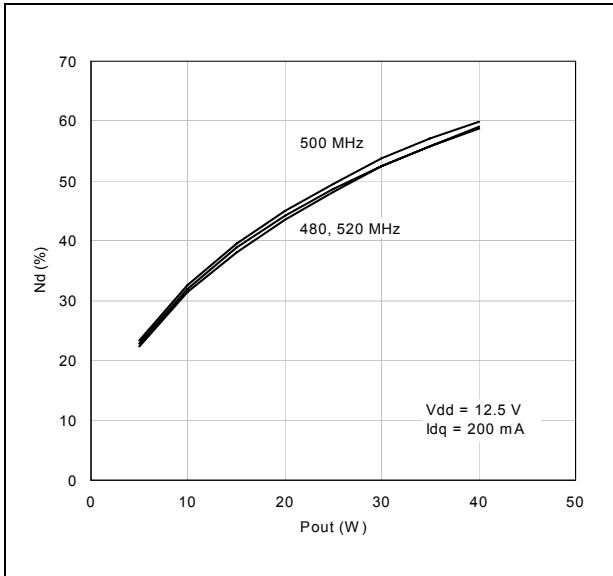


Figure 10. Input return loss vs output power

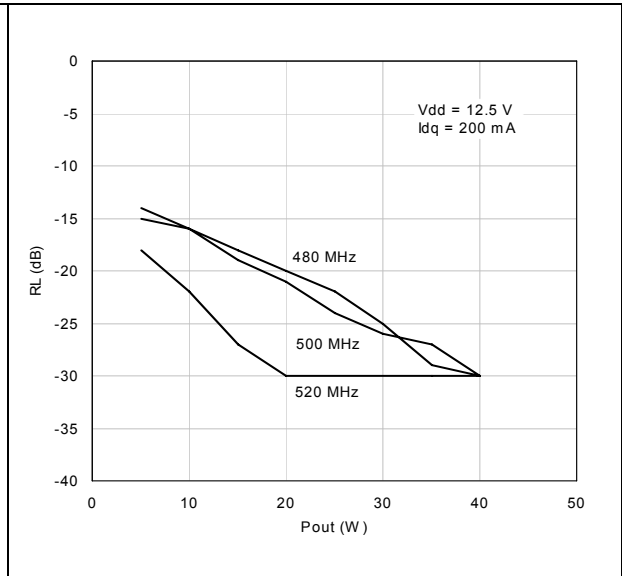


Figure 11. Output power vs bias current

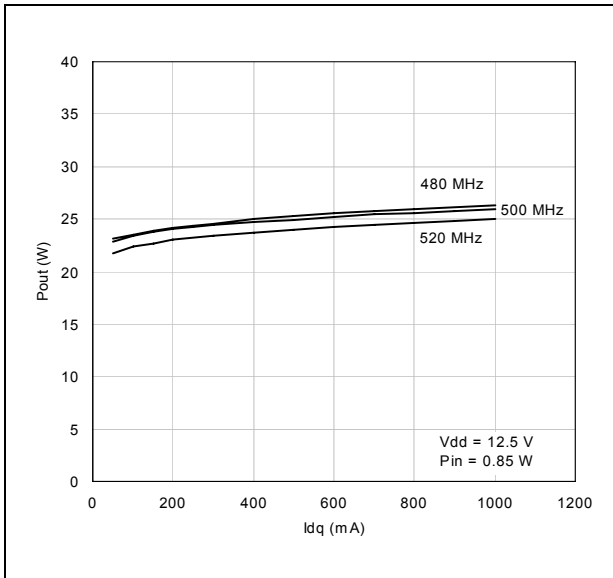


Figure 12. Drain efficiency vs bias current

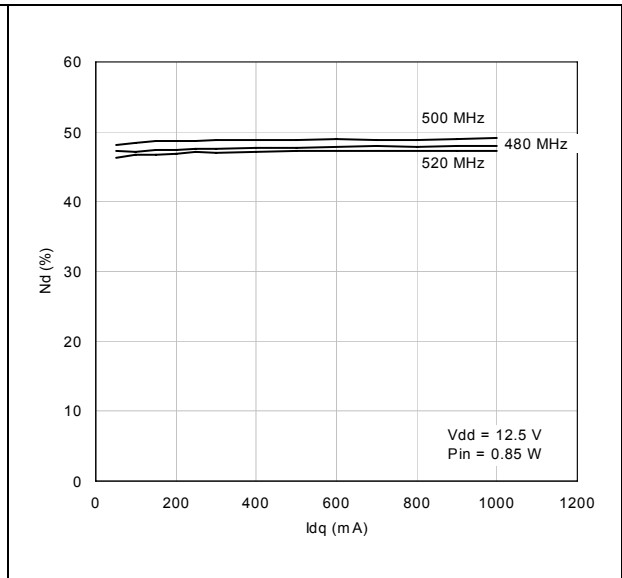


Figure 13. Output power vs supply voltage

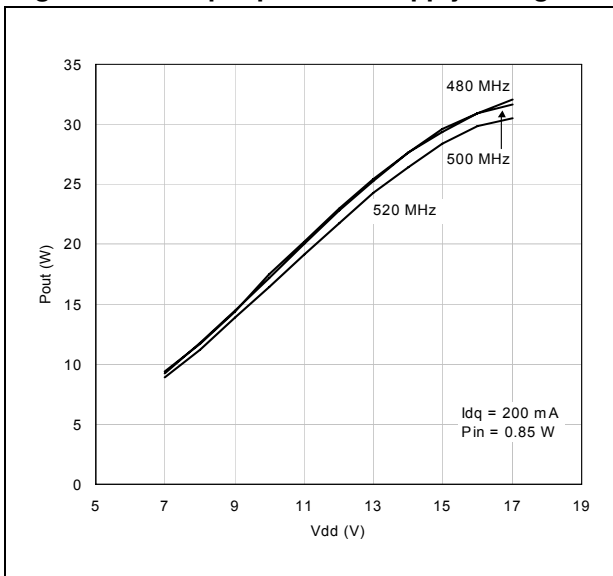


Figure 14. Drain efficiency vs supply voltage

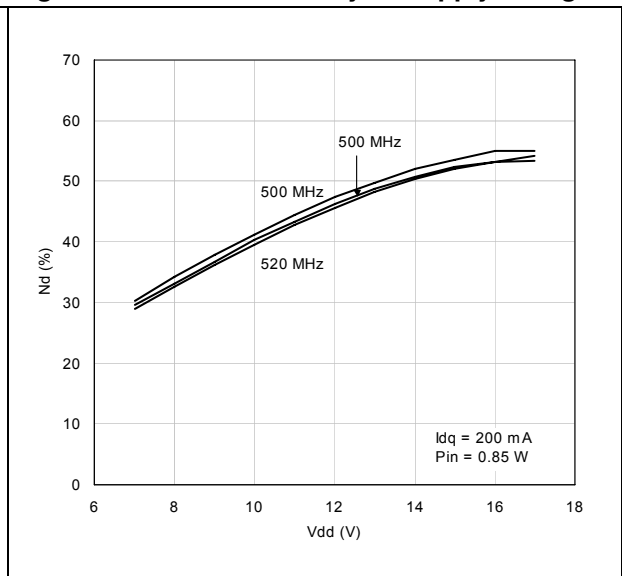


Figure 15. Output power vs gate bias voltage

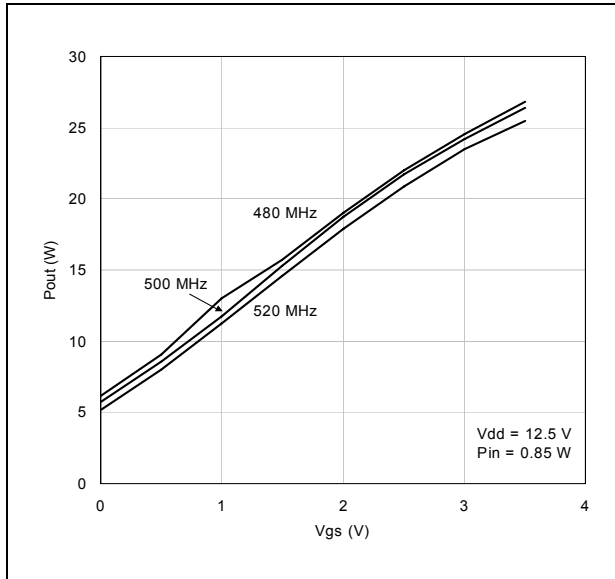


Figure 16. Output power vs input power (f = 175 MHz)

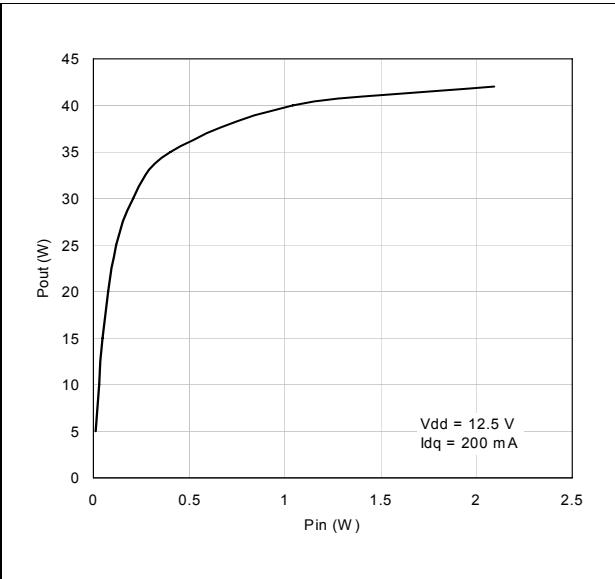


Figure 17. Power gain vs output power (f = 175 MHz)

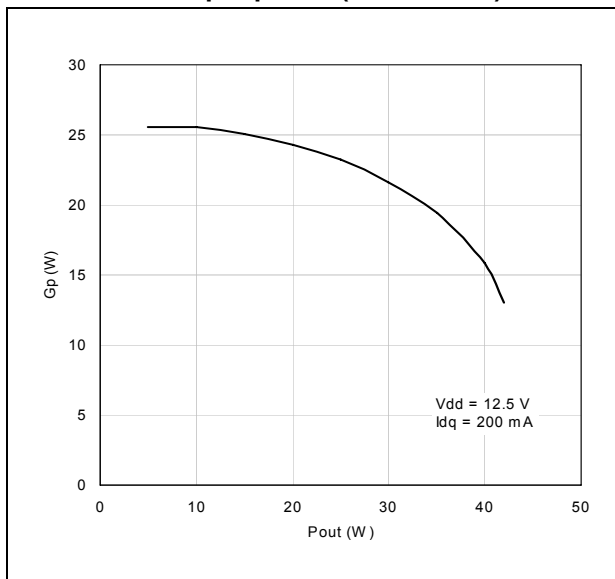


Figure 18. Drain efficiency vs output power (f = 175 MHz)

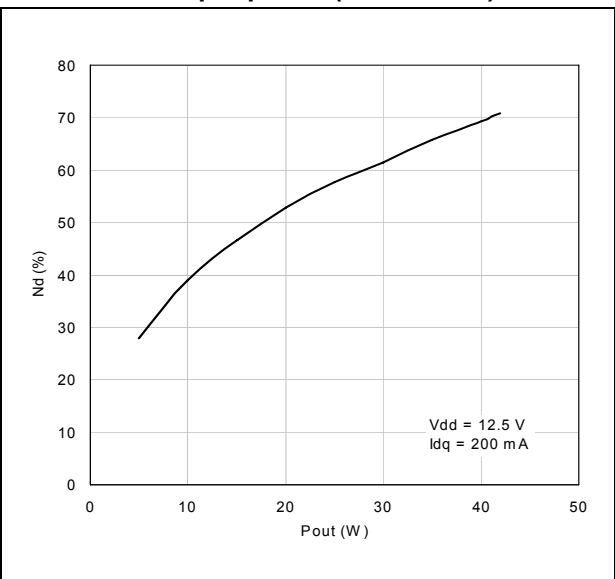
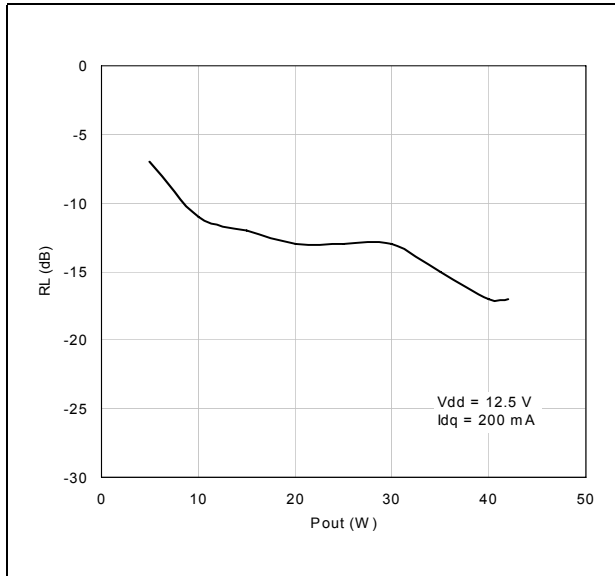


Figure 19. Input return loss vs output power
(f = 175 MHz)



5 Test circuit

Figure 20. 500 MHz test circuit schematic (engineering)

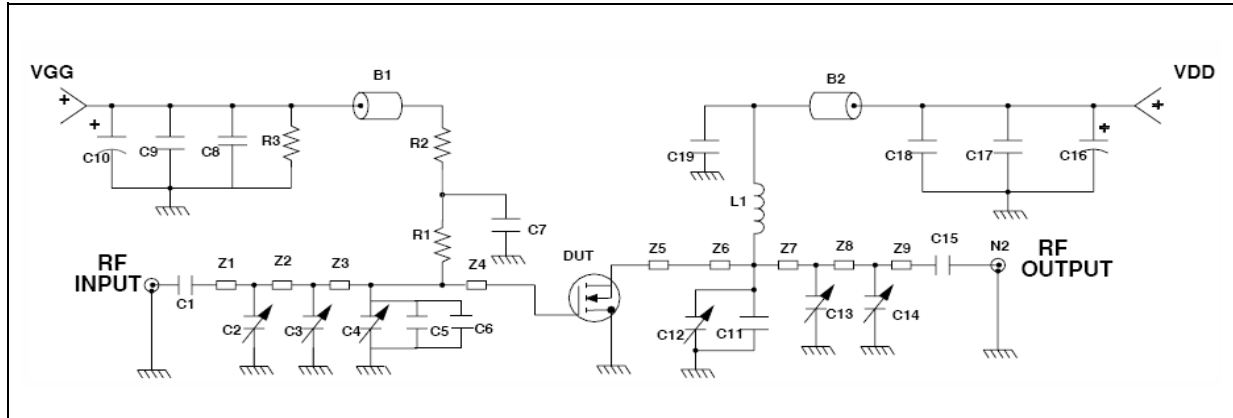


Table 8. Test circuit component part list

Component	Description
B1,B2	Ferrite bead
C1,C13	300 pF, 100 mil chip capacitor
C2,C3,C4,C12,C13,C14	1 to 20 pF trimmer capacitor
C6	39 pF ATC 100B surface mount ceramic chip capacitor
C7, C19	120 pF 100 mil chip capacitor
C10, C16	10 μF, 50 V electrolytic capacitor
C9, C17	0.1 mF, 100 mil chip cap
C8, C18	1.000 pF 100 mil chip cap
C5, C11	33 pF, 100 mil chip cap
L1	56 nH, 7 TURN, Coilcraft
N1, N2	Type N flange mount
R1	15 Ω, 1 W chip resistor
R2	1 kΩ, 1 W chip resistor
R3	33 kΩ, 1 W chip resistor
Z1	0.471" X 0.080" microstrip
Z2	1.082" X 0.080" microstrip
Z3	0.372" X 0.080" microstrip
Z4,Z5	0.260" X 0.223" microstrip
Z6	0.050" X 0.080" microstrip
Z7	0.551" X 0.080" microstrip
Z8	0.825" X 0.080" microstrip
Z9	0.489" X 0.080" microstrip
Board	Roger, ultra lam 2000 THK 0.030", εr = 2.55 2oz. ED cu 2 Sides.

6 Circuit layout

Figure 21. 500 MHz test circuit

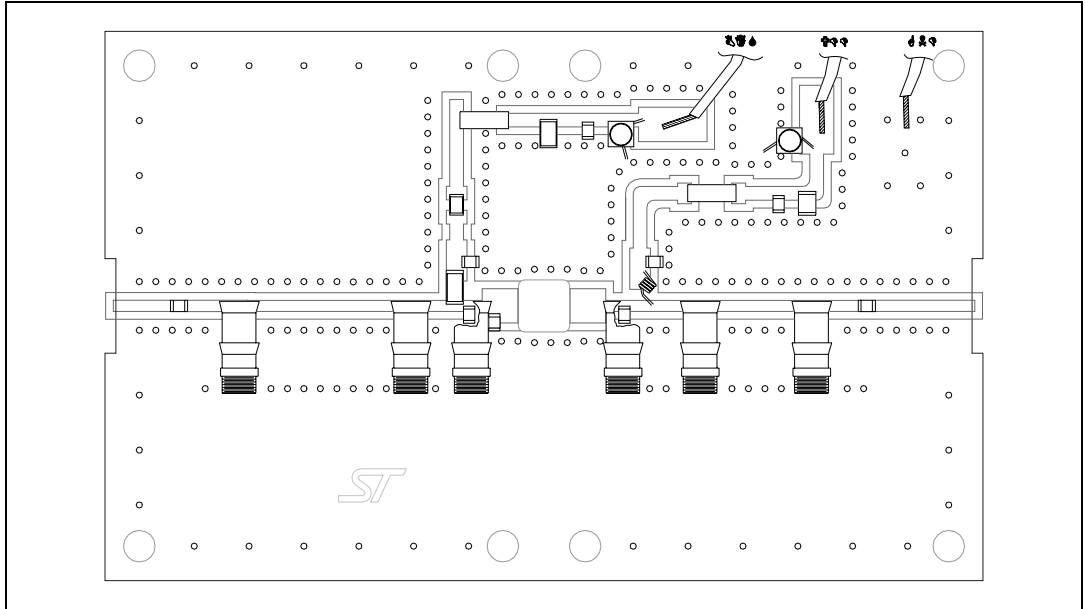


Figure 22. 500 MHz test circuit photomaster

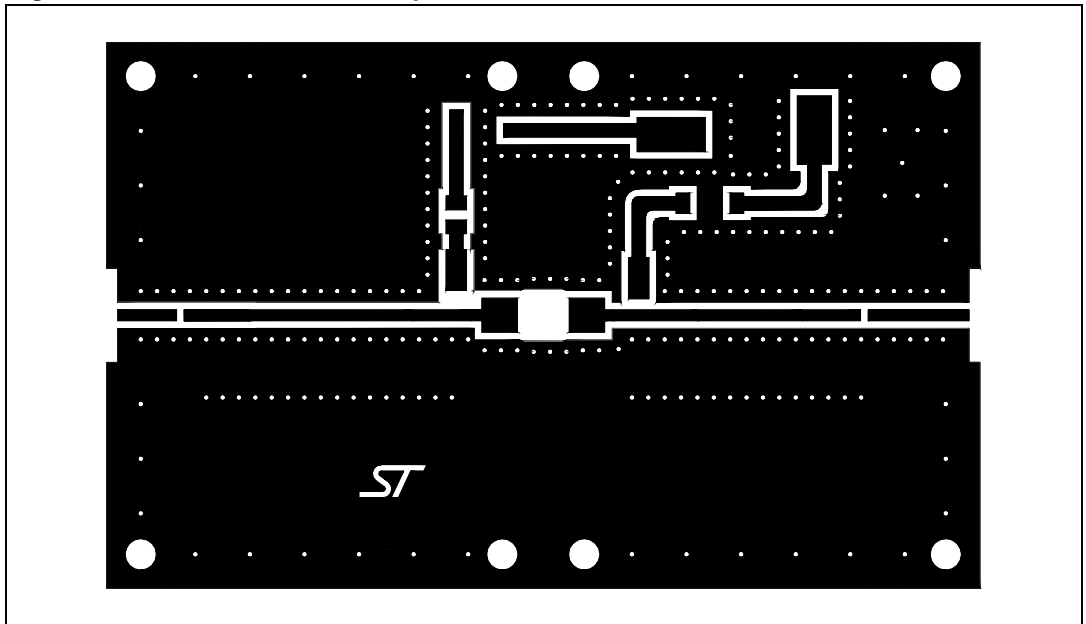


Figure 23. 175 MHz test circuit schematic (engineering)

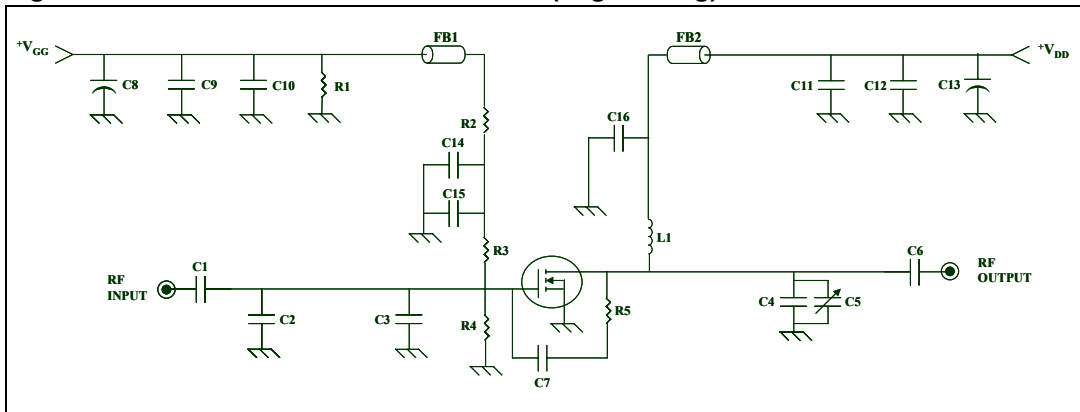


Table 9. 175 MHz test circuit component part list

Component	Description
C1, C6	300 pF chip capacitor
C2, C3	91 pF chip capacitor
C4, C14	75 pF chip capacitor
C5	1-20 pF trimmer capacitor
C7	.01 µF molded capacitor
C8, C13	10 µF electrolytic capacitor
C9, C12	.1 µF chip capacitor
C10, C11	1000 pF chip capacitor
C15, C16	1200 pF chip capacitor
FB1, FB2	Ferrite bead
R1	33 kΩ chip resistor
R2	17 Ω chip resistor
R3	15 Ω chip resistor
R4	47 Ω chip resistor
R5	220 Ω chip resistor
L1	5 turn, 16 AWG magnet wire, ID = .40", inductor
Board	Roger, ultra lam 2000, THK 0.030", εr = 2.55 2oz. ED cu 2 SIDES.

7 Common source s-parameter

Table 10. S-parameter for PD55025S-E ($V_{DS} = 12.5\text{ V}$ $I_D = 500\text{ mA}$)

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
50	0.837	-162	13.33	89	0.018	-1	0.780	-168
100	0.846	-169	6.51	76	0.017	-12	0.803	-172
150	0.862	-171	4.15	66	0.016	-19	0.831	-172
200	0.878	-173	2.93	58	0.015	-26	0.859	-172
250	0.895	-174	2.20	51	0.013	-31	0.874	-172
300	0.910	-174	1.71	45	0.012	-36	0.886	-173
350	0.921	-175	1.36	40	0.010	-40	0.892	-173
400	0.932	-176	1.11	35	0.009	-42	0.897	-175
450	0.941	-177	0.92	31	0.008	-43	0.915	-176
500	0.946	-178	0.78	27	0.007	-44	0.932	-177
550	0.953	-178	0.66	24	0.006	-43	0.946	-178
600	0.957	-179	0.57	21	0.005	-42	0.964	-179
650	0.960	-180	0.50	18	0.004	-39	0.975	-178
700	0.964	180	0.44	16	0.004	-34	0.976	-179
750	0.966	179	0.39	14	0.003	-29	0.981	-179
800	0.968	178	0.35	12	0.002	-15	0.979	-179
850	0.970	178	0.31	10	0.002	-2	0.964	-179
900	0.971	177	0.28	8	0.002	16	0.960	180
950	0.972	177	0.26	6	0.002	34	0.953	179
1000	0.972	176	0.23	5	0.003	45	0.940	178

Table 11. S-parameter PD55025S-E ($V_{DS} = 12.5\text{ V}$ $I_D = 1.5\text{ A}$)

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
50	0.876	-164	13.87	90	0.013	1	0.823	-172
100	0.880	-172	6.87	79	0.012	-7	0.838	-175
150	0.887	-174	4.46	71	0.012	-13	0.855	-176
200	0.895	-175	3.22	64	0.011	-18	0.873	-175
250	0.905	-176	2.47	58	0.010	-22	0.879	-175
300	0.915	-176	1.96	52	0.009	-25	0.885	-175
350	0.922	-177	1.60	47	0.009	-28	0.886	-175

Table 11. S-parameter PD55025S-E ($V_{DS} = 12.5\text{ V}$ $I_D = 1.5\text{ A}$) (continued)

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
400	0.931	-178	1.32	42	0.008	-30	0.889	-177
450	0.938	-178	1.11	38	0.007	-31	0.906	-178
500	0.942	-179	0.95	34	0.006	-31	0.923	-179
550	0.948	-179	0.82	31	0.005	-30	0.937	-179
600	0.952	-180	0.71	28	0.005	-27	0.956	-179
650	0.954	180	0.63	25	0.004	-22	0.967	-179
700	0.959	179	0.55	22	0.003	-16	0.969	-179
750	0.961	178	0.49	20	0.003	-6	0.973	-179
800	0.963	178	0.45	17	0.003	3	0.970	-179
850	0.966	177	0.40	15	0.003	17	0.956	-180
900	0.967	177	0.36	13	0.003	27	0.952	179
950	0.968	176	0.33	11	0.003	38	0.945	179
1000	0.968	176	0.30	9	0.003	45	0.933	177

Table 12. S-parameter for PD55025S-E ($V_{DS} = 12.5\text{ V}$ $I_D = 3\text{ A}$)

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
50	0.890	-165	13.19	91	0.012	2	0.837	-174
100	0.892	-172	6.55	81	0.011	-6	0.846	-176
150	0.898	-174	4.28	73	0.011	-12	0.865	-176
200	0.904	-175	3.11	66	0.010	-15	0.879	-176
250	0.913	-176	2.39	60	0.010	-20	0.883	-176
300	0.921	-177	1.91	54	0.009	-23	0.089	-176
350	0.926	-177	1.57	49	0.008	-25	0.887	-176
400	0.935	-178	1.31	44	0.007	-27	0.889	-177
450	0.941	-179	1.10	40	0.007	-28	0.905	-179
500	0.944	-179	0.94	36	0.006	-27	0.921	-179
550	0.949	-180	0.82	33	0.005	-25	0.936	-180
600	0.953	180	0.71	29	0.004	-21	0.954	180
650	0.955	179	0.63	26	0.004	-17	0.964	-180
700	0.959	179	0.56	24	0.003	-10	0.965	-180
750	0.961	178	0.50	21	0.003	-2	0.968	-180
800	0.963	177	0.45	19	0.003	10	0.966	-179
850	0.966	177	0.41	17	0.003	22	0.952	-180

Table 12. S-parameter for PD55025S-E ($V_{DS} = 12.5 \text{ V}$ $I_D = 3 \text{ A}$) (continued)

Freq (MHz)	$ S_{11} $	$S_{11} < \Phi$	$ S_{21} $	$S_{21} < \Phi$	$ S_{12} $	$S_{12} < \Phi$	$ S_{22} $	$S_{22} < \Phi$
900	0.967	176	0.37	15	0.003	32	0.948	180
950	0.968	176	0.34	15	0.003	41	0.942	179
1000	0.969	175	0.31	11	0.004	49	0.930	177

Table 13. S-parameter for PD55025S-E ($V_{DS} = 13.8 \text{ V}$ $I_D = 3 \text{ A}$)

Freq (MHz)	$ S_{11} $	$S_{11} < \Phi$	$ S_{21} $	$S_{21} < \Phi$	$ S_{12} $	$S_{12} < \Phi$	$ S_{22} $	$S_{22} < \Phi$
50	0.849	-164	13.99	91	0.012	2	0.833	-173
100	0.881	-171	6.94	80	0.011	-6	0.841	-175
150	0.895	-173	4.51	72	0.011	-12	0.857	-175
200	0.903	-175	3.27	65	0.010	-16	0.871	-175
250	0.912	-176	2.50	58	0.010	-21	0.877	-175
300	0.921	-176	1.99	52	0.009	-24	0.882	-175
350	0.927	-177	1.62	47	0.008	-27	0.883	-176
400	0.936	-178	1.35	42	0.007	-29	0.886	-177
450	0.943	-178	1.13	38	0.006	-29	0.904	-178
500	0.946	-179	0.97	34	0.006	-29	0.920	-179
550	0.952	-180	0.83	31	0.005	-26	0.935	-179
600	0.955	180	0.72	27	0.004	-23	0.955	-180
650	0.957	179	0.64	24	0.004	-17	0.965	-179
700	0.961	179	0.56	22	0.003	-8	0.967	-179
750	0.963	178	0.50	19	0.003	2	0.970	-179
800	0.965	178	0.45	17	0.003	14	0.968	-179
850	0.968	177	0.41	15	0.003	27	0.953	-179
900	0.969	176	0.37	13	0.003	36	0.949	180
950	0.970	176	0.34	11	0.003	45	0.943	179
1000	0.971	175	0.31	9	0.003	54	0.930	178

8 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 14. PowerSO-10RF formed lead (Gull Wing) mechanical data

Dim.	mm.			Inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A1	0	0.05	0.1	0.	0.0019	0.0038
A2	3.4	3.5	3.6	0.134	0.137	0.142
A3	1.2	1.3	1.4	0.046	0.05	0.054
A4	0.15	0.2	0.25	0.005	0.007	0.009
a		0.2			0.007	
b	5.4	5.53	5.65	0.212	0.217	0.221
c	0.23	0.27	0.32	0.008	0.01	0.012
D	9.4	9.5	9.6	0.370	0.374	0.377
D1	7.4	7.5	7.6	0.290	0.295	0.298
E	13.85	14.1	14.35	0.544	0.555	0.565
E1	9.3	9.4	9.5	0.365	0.37	0.375
E2	7.3	7.4	7.5	0.286	0.292	0.294
E3	5.9	6.1	6.3	0.231	0.24	0.247
F		0.5			0.019	
G		1.2			0.047	
L	0.8	1	1.1	0.030	0.039	0.042
R1			0.25			0.01
R2		0.8			0.031	
T	2 deg	5 deg	8 deg	2 deg	5 deg	8 deg
T1		6 deg			6 deg	
T2		10 deg			10 deg	

Note: Resin protrusions not included (max value: 0.15 mm per side)

Figure 24. Package dimensions PowerSO-10RF formed lead

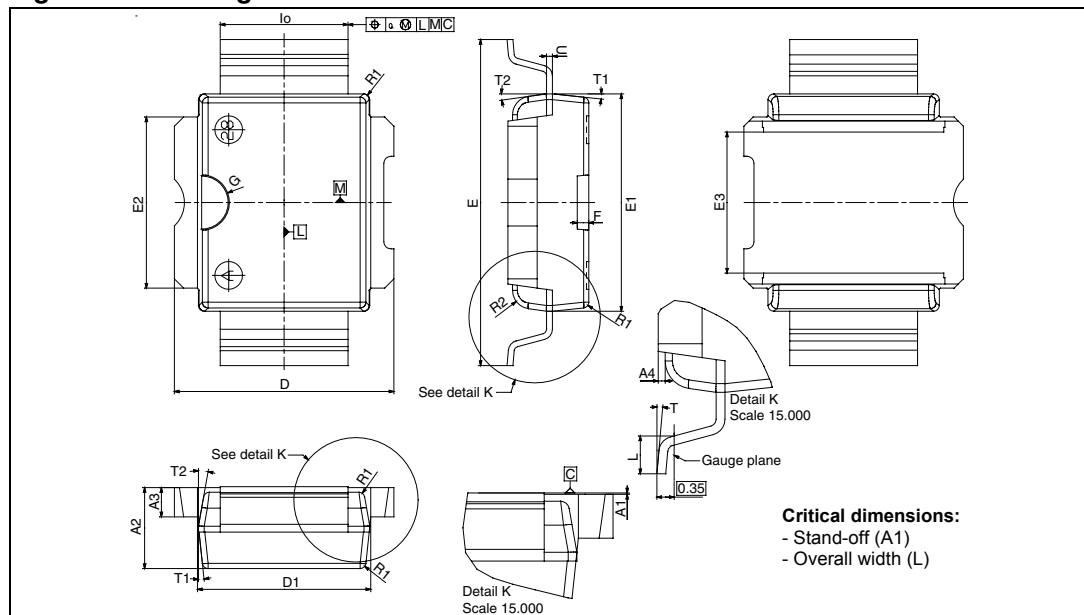


Table 15. PowerSO-10RF straight lead mechanical data

Dim.	mm.			Inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A1	1.62	1.67	1.72	0.064	0.065	0.068
A2	3.4	3.5	3.6	0.134	0.137	0.142
A3	1.2	1.3	1.4	0.046	0.05	0.054
A4	0.15	0.2	0.25	0.005	0.007	0.009
a		0.2			0.007	
b	5.4	5.53	5.65	0.212	0.217	0.221
c	0.23	0.27	0.32	0.008	0.01	0.012
D	9.4	9.5	9.6	0.370	0.374	0.377
D1	7.4	7.5	7.6	0.290	0.295	0.298
E	15.15	15.4	15.65	0.595	0.606	0.615
E1	9.3	9.4	9.5	0.365	0.37	0.375
E2	7.3	7.4	7.5	0.286	0.292	0.294
E3	5.9	6.1	6.3	0.231	0.24	0.247
F		0.5			0.019	
G		1.2			0.047	
R1			0.25			0.01
R2		0.8			0.031	
T1		6 deg			6 deg	
T2		10 deg			10 deg	

Note: Resin protrusions not included (max value: 0.15 mm per side)

Figure 25. Package dimensions PowerSO-10RF straight lead

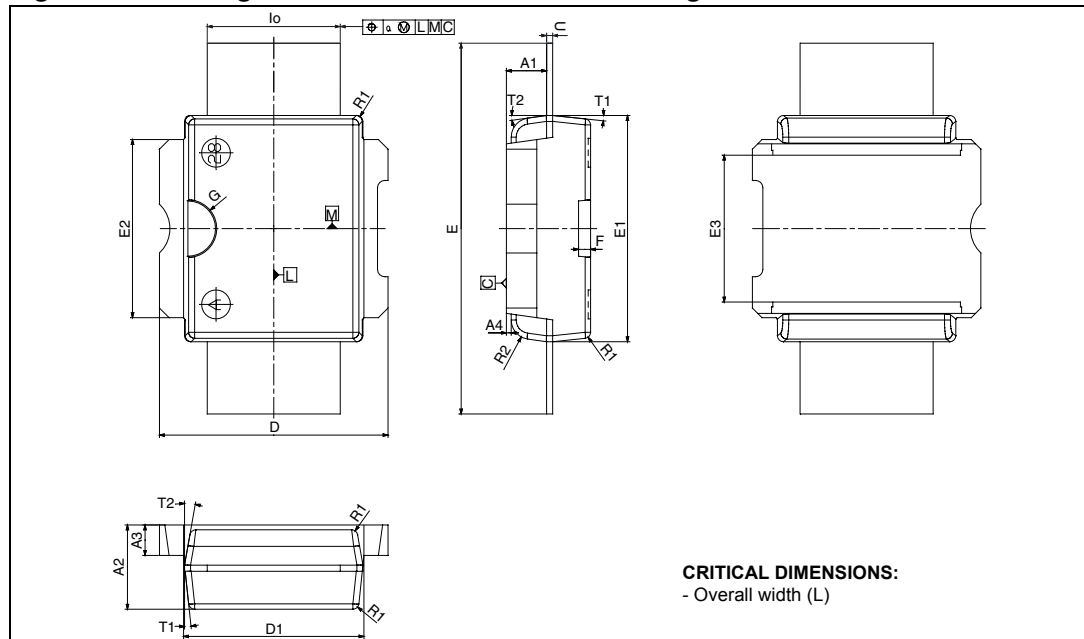


Figure 26. Tube information

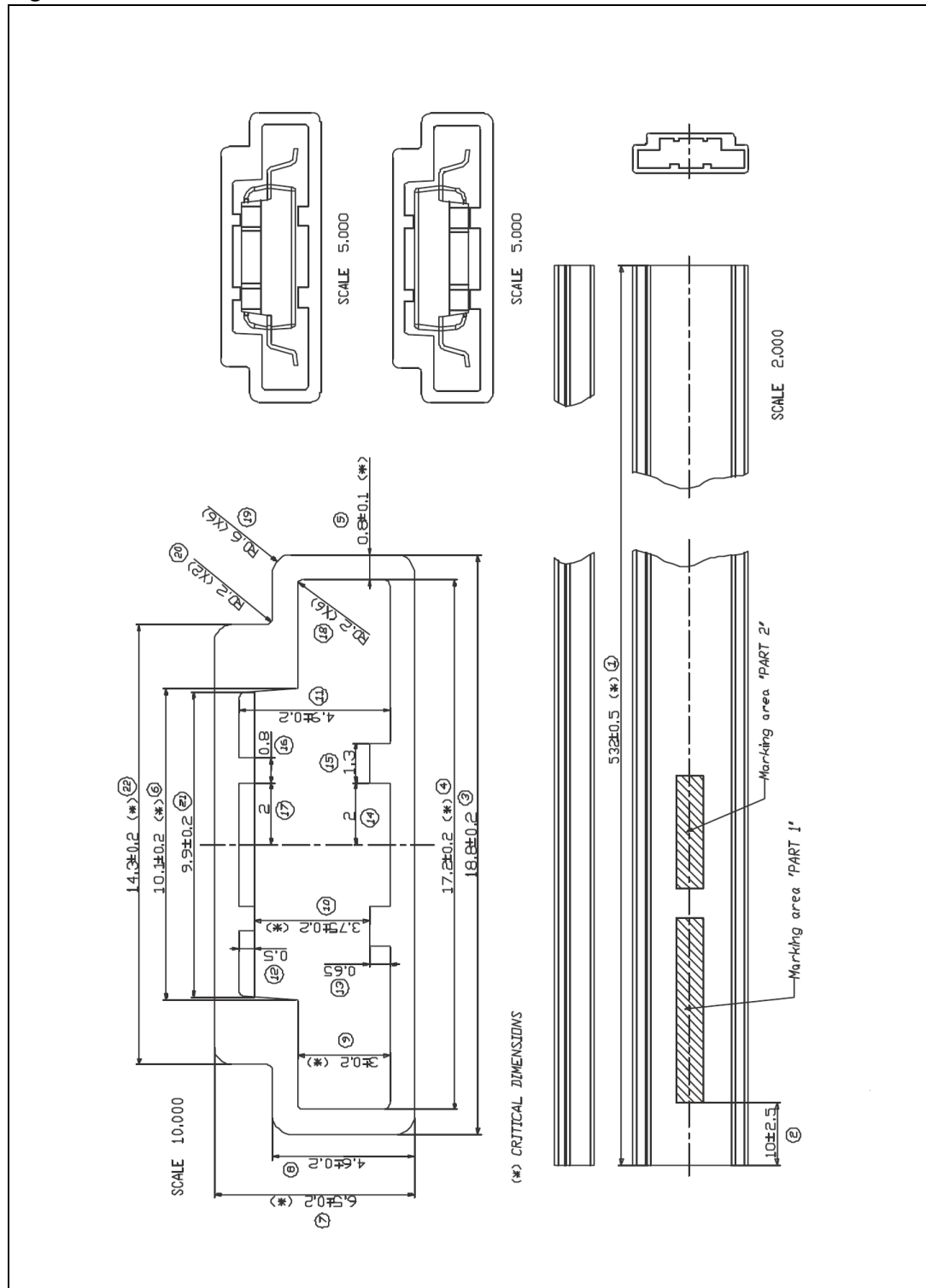
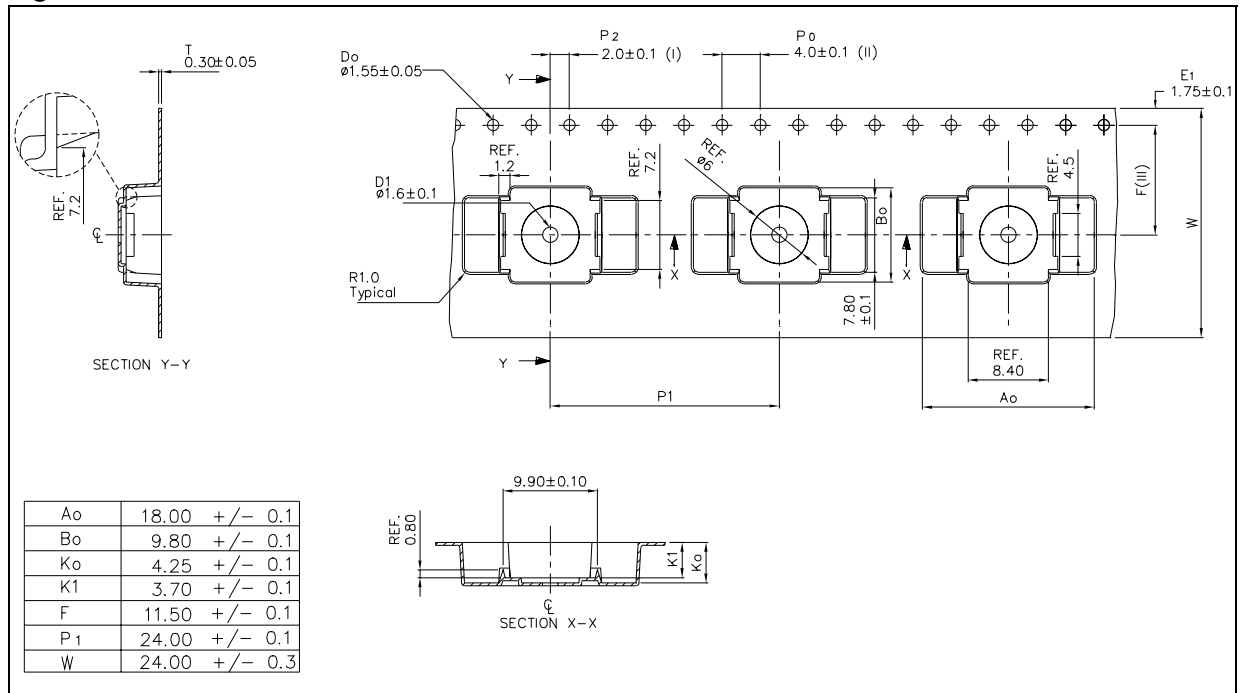


Figure 27. Reel information



9 Revision history

Table 16. Document revision history

Date	Revision	Changes
29-Apr-2006	1	Initial release.
03-Jun-2010	2	Added: Table 6: Moisture sensitivity level .

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2010 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com





Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.